

Long Shibing

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/584056/publications.pdf>

Version: 2024-02-01

57
papers

3,196
citations

136950

32
h-index

161849

54
g-index

57
all docs

57
docs citations

57
times ranked

2349
citing authors

#	ARTICLE	IF	CITATIONS
1	Photovoltageâ€Competing Dynamics in Photoelectrochemical Devices: Achieving Selfâ€Powered Spectrally Distinctive Photodetection. <i>Advanced Functional Materials</i> , 2022, 32, .	14.9	30
2	Highâ€Performance Harshâ€Environmentâ€Resistant GaO_X Solarâ€Blind Photodetectors via Defect and Doping Engineering. <i>Advanced Materials</i> , 2022, 34, e2106923.	21.0	83
3	One Transistor One Electrolyte-Gated Transistor for Supervised Learning in SNNs. <i>IEEE Electron Device Letters</i> , 2022, 43, 296-299.	3.9	6
4	Over 1 GW/cm₂ Vertical Ga₂O₃ Schottky Barrier Diodes Without Edge Termination. <i>IEEE Electron Device Letters</i> , 2022, 43, 264-267.	3.9	34
5	æ°Sâ€CEâ€é.â€“â€Ÿâ€â™™â€»¶â€¼,è`ç•CEéé™.é±â€†â€° çš,,æâ€-æ-1æ³•. <i>Scientia Sinica: Physica, Mechanica Et Astronomica</i> , 2022, , 0		
6	Hysteresis-free Ga2O3 solar-blind phototransistor modulated from photoconduction to photogating effect. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	13
7	Achieving Record High External Quantum Efficiency >86.7% in Solarâ€Blind Photoelectrochemical Photodetection. <i>Advanced Functional Materials</i> , 2022, 32, .	14.9	23
8	Leakage current suppression and breakdown voltage enhancement in GaN-on-GaN vertical Schottky barrier diodes enabled by oxidized platinum as Schottky contact metal. <i>Semiconductor Science and Technology</i> , 2022, 37, 065010.	2.0	2
9	Elevated barrier height originated from electric dipole effect and improved breakdown characteristics in PtO_x/Î²-Ga₂O₃ Schottky barrier diodes. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 304003.	2.8	7
10	Positive-Bias Stress Stability of Solution-Processed Oxide Semiconductor Thin-Film Transistor. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 3727-3731.	3.0	2
11	Aqueousâ€Printed Ga₂O₃ Films for Highâ€Performance Flexible and Heatâ€Resistant Deep Ultraviolet Photodetector and Array. <i>Advanced Optical Materials</i> , 2022, 10, .	7.3	24
12	Correlation Between Electrical Performance and Gate Width of GaN-Based HEMTs. <i>IEEE Electron Device Letters</i> , 2022, 43, 1199-1202.	3.9	8
13	Experimental Investigation on Threshold Voltage Instability for <i>Î²</i>-Ga₂O₃ MOSFET Under Electrical and Thermal Stress. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 5048-5054.	3.0	6
14	Normally-off Î²-Ga₂O₃ Power Heterojunction Field-Effect-Transistor Realized by p-NiO and Recessed-Gate. , 2022, , .		13
15	2.6 kV NiO/Ga₂O₃ Heterojunction Diode with Superior High-Temperature Voltage Blocking Capability. , 2022, , .		20
16	Observation of polarity-switchable photoconductivity in III-nitride/MoSx core-shell nanowires. <i>Light: Science and Applications</i> , 2022, 11, .	16.6	38
17	Controlling different phases of gallium oxide for solar-blind photodetector application. <i>Semiconductors and Semimetals</i> , 2021, 107, 101-151.	0.7	4
18	Low defect density and small Iâ€V curve hysteresis in NiO/ <i>Î²</i>-Ga2O3 pn diode with a high PFOM of 0.65 GW/cm2. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	92

#	ARTICLE	IF	CITATIONS
19	Double-Barrier $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky Barrier Diode With Low Turn-on Voltage and Leakage Current. IEEE Electron Device Letters, 2021, 42, 430-433.	3.9	37
20	High-Detectivity $\text{In}^2\text{-Ga}_2\text{O}_3$ Microflake Solar-Blind Phototransistor for Weak Light Detection. IEEE Electron Device Letters, 2021, 42, 383-386.	3.9	40
21	Investigation of quantum structure in N-polar deep-ultraviolet light-emitting diodes. Journal of Applied Physics, 2021, 129, .	2.5	7
22	Realizing High-Performance $\text{In}^2\text{-Ga}_2\text{O}_3$ MOSFET by Using Variation of Lateral Doping: A TCAD Study. IEEE Transactions on Electron Devices, 2021, 68, 1501-1506.	3.0	37
23	Balancing the Transmittance and Carrier Collection Ability of Ag Nanowire Networks for High-Performance Self-Powered Ga_2O_3 Schottky Photodiode. Advanced Optical Materials, 2021, 9, 2100173.	7.3	32
24	Tuning the Charge Transfer Dynamics of the Nanostructured GaN Photoelectrodes for Efficient Photoelectrochemical Detection in the Ultraviolet Band. Advanced Functional Materials, 2021, 31, 2103007.	14.9	50
25	Demonstration of AlGaIn/GaN-based ultraviolet phototransistor with a record high responsivity over 3.6×10^7 A/W. Applied Physics Letters, 2021, 118, .	3.3	74
26	Demonstration of AlGaIn/GaN HEMTs on vicinal sapphire substrates with large misoriented angles. Applied Physics Letters, 2021, 119, .	3.3	8
27	Fully Printed High-Performance n-Type Metal Oxide Thin-Film Transistors Utilizing Coffee-Ring Effect. Nano-Micro Letters, 2021, 13, 164.	27.0	30
28	Ultra-High Performance Amorphous Ga_2O_3 Photodetector Arrays for Solar-Blind Imaging. Advanced Science, 2021, 8, e2101106.	11.2	91
29	A unified hybrid compact model of $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes for mixer and rectifier applications. Science China Information Sciences, 2021, 64, 1.	4.3	5
30	Bidirectional photocurrent in $\text{In}^2\text{-Ga}_2\text{O}_3$ heterojunction nanowires. Nature Electronics, 2021, 4, 645-652.	26.0	129
31	High-Performance $\text{In}^2\text{-Ga}_2\text{O}_3$ Solar-Blind Photodetector With Extremely Low Working Voltage. IEEE Electron Device Letters, 2021, 42, 1492-1495.	3.9	23
32	Review of polymorphous Ga_2O_3 materials and their solar-blind photodetector applications. Journal Physics D: Applied Physics, 2021, 54, 043001.	2.8	98
33	Toward emerging gallium oxide semiconductors: A roadmap. Fundamental Research, 2021, 1, 697-716.	3.3	56
34	Coupling Plasmonic Pt Nanoparticles with AlGaIn Nanostructures for Enhanced Broadband Photoelectrochemical-Detection Applications. ACS Applied Nano Materials, 2021, 4, 13938-13946.	5.0	15
35	Evolution of the conductive filament system in HfO ₂ -based memristors observed by direct atomic-scale imaging. Nature Communications, 2021, 12, 7232.	12.8	85
36	Band engineering of III-nitride-based deep-ultraviolet light-emitting diodes: a review. Journal Physics D: Applied Physics, 2020, 53, 073002.	2.8	102

#	ARTICLE	IF	CITATIONS
37	Enhancement-Mode $\text{AlN}/\text{Ga}_2\text{O}_3$ Metal-Oxide-Semiconductor Field-Effect Transistor with High Breakdown Voltage over 3000V Realized by Oxygen Annealing. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020, 14, 1900586.	2.4	39
38	High-Voltage (10^1) Ga_2O_3 Vertical Schottky Barrier Diode With Thermally-Oxidized Termination. <i>IEEE Electron Device Letters</i> , 2020, 41, 131-134.	3.9	52
39	Normally-off $\text{AlN}/\text{Ga}_2\text{O}_3$ field-effect transistors using polarization-induced doping. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 345107.	2.8	24
40	Metal-Semiconductor-Metal $\mu\text{-Ga}_2\text{O}_3$ Solar-Blind Photodetectors with a Record-High Responsivity Rejection Ratio and Their Gain Mechanism. <i>ACS Photonics</i> , 2020, 7, 812-820.	6.6	152
41	Fast Switching Ga_2O_3 Power MOSFET With a Trench-Gate Structure. <i>IEEE Electron Device Letters</i> , 2019, 40, 1385-1388.	3.9	46
42	High-Performance Metal-Organic Chemical Vapor Deposition Grown Ga_2O_3 Solar-Blind Photodetector With Asymmetric Schottky Electrodes. <i>IEEE Electron Device Letters</i> , 2019, 40, 1475-1478.	3.9	91
43	Unambiguously Enhanced Ultraviolet Luminescence of AlGaN Wavy Quantum Well Structures Grown on Large Misoriented Sapphire Substrate. <i>Advanced Functional Materials</i> , 2019, 29, 1905445.	14.9	128
44	Ultrahigh-Performance Solar-Blind Photodetector Based on α -Phase-Dominated Ga_2O_3 Film With Record Low Dark Current of 81 fA. <i>IEEE Electron Device Letters</i> , 2019, 40, 1483-1486.	3.9	58
45	Enhanced Performance of an AlGaN-Based Deep-Ultraviolet LED Having Graded Quantum Well Structure. <i>IEEE Photonics Journal</i> , 2019, 11, 1-6.	2.0	36
46	Amorphous Gallium Oxide-Based Gate-Tunable High-Performance Thin Film Phototransistor for Solar-Blind Imaging. <i>Advanced Electronic Materials</i> , 2019, 5, 1900389.	5.1	95
47	Review of deep ultraviolet photodetector based on gallium oxide. <i>Chinese Physics B</i> , 2019, 28, 018501.	1.4	85
48	Enhancement-Mode Ga_2O_3 Metal-Oxide-Semiconductor Field-Effect Solar-Blind Phototransistor With Ultrahigh Detectivity and Photo-to-Dark Current Ratio. <i>IEEE Electron Device Letters</i> , 2019, 40, 742-745.	3.9	55
49	An improved analytical model for the statistics of SET emergence point in HfO ₂ memristive device. <i>AIP Advances</i> , 2019, 9, 025118.	1.3	1
50	Advantages of AlGaN-based deep-ultraviolet light-emitting diodes with an Al-composition graded quantum barrier. <i>Optics Express</i> , 2019, 27, A1544.	3.4	53
51	Characterization of the inhomogeneous barrier distribution in a Pt/(100) Ga_2O_3 Schottky diode via its temperature-dependent electrical properties. <i>AIP Advances</i> , 2018, 8, .	1.3	56
52	Schottky Barrier Rectifier Based on (100) Ga_2O_3 and its DC and AC Characteristics. <i>IEEE Electron Device Letters</i> , 2018, 39, 556-559.	3.9	50
53	An Overview of the Ultrawide Bandgap Ga_2O_3 Semiconductor-Based Schottky Barrier Diode for Power Electronics Application. <i>Nanoscale Research Letters</i> , 2018, 13, 290.	5.7	155
54	Resistive Switching: Breaking the Current-Retention Dilemma in Cation-Based Resistive Switching Devices Utilizing Graphene with Controlled Defects (<i>Adv. Mater.</i> 14/2018). <i>Advanced Materials</i> , 2018, 30, 1870100.	21.0	4

#	ARTICLE	IF	CITATIONS
55	C-V and J-V investigation of HfO ₂ /Al ₂ O ₃ bilayer dielectrics MOSCAPs on (100) λ^2 -Ga ₂ O ₃ . AIP Advances, 2018, 8, .	1.3	40
56	Schottky barrier diode based on λ^2 -Ga ₂ O ₃ (100) single crystal substrate and its temperature-dependent electrical characteristics. Applied Physics Letters, 2017, 110, .	3.3	132
57	Real-Time Observation on Dynamic Growth/Dissolution of Conductive Filaments in Oxide-Electrolyte-Based ReRAM. Advanced Materials, 2012, 24, 1844-1849.	21.0	520